

Specification Amendments

Please replace the paragraph beginning on page 13, line 32, with the amended paragraph, as follows:

During the read function, the light emitters 43 emit a lower level energy field to locally excite charge carriers in the LASL ~~4732~~ of the diode 41, as discussed with respect to Figure ~~42~~. The amount of the beam that reaches the LASL ~~4732~~ will depend on the state of the storage area 45. Thus the storage layer acts primarily as a variable absorber or reflector of the beam during the read stage, depending on the state of the storage area. An additional field may be applied across interface 47 by a voltage source 48. The current that results from carriers passing across the diode interface between layer 47 and layer 44 can be monitored by a detection signal 49 taken across the interface between layer 47 and layer 44 to determine the state of data storage areas 45. Alternatively, the open circuit photo-voltage generated across diode 41 could be monitored.